Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1668	transistor same (workfunction work adj function)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:22
L2	9	1 and (workfunction work adj function) with dominat$4	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:35
L3	312	1 and (workfunction work adj function) with (poly polysilicon) near3 gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:36
L4	36	3 and (barrier) with (poly polysilicon) near3 gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:57
L5	25	09/943134	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:51
L6	1577	mos with polysilicon adj gate	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:58
L7	25	mos with (polysilicon adj gate) with (workfunction work adj function)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:58
S41	1668	transistor same (workfunction work adj function)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:22
S42	1083	transistor with (workfunction work adj function)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/13 10:47
S44	784	S42 and (transistor workfunction work adj function) with oxide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/13 10:48

S45	132	S44 and (transistor workfunction work adj function) with barrier	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/13 10:50
S46	132	S45 and (transistor workfunction work adj function) with barrier	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/13 10:52
S47	5	transistor same (workfunction work adj function) with dominat$4	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/14 06:23
S48	22	(workfunction work adj function) with dominat$4	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/12/13 16:29